

Jinn-Kong Sheu

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#	Paper	IF	Citations
285	White-light emission from near UV InGaN-GaN LED chip precoated with blue/green/red phosphors. <i>IEEE Photonics Technology Letters</i> , 2003 , 15, 18-20	2.2	546
284	400-nm InGaN-GaN and InGaN-AlGaN multiquantum well light-emitting diodes. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2002 , 8, 744-748	3.8	196
283	Effects of thermal annealing on the indium tin oxide Schottky contacts of n-GaN. <i>Applied Physics Letters</i> , 1998 , 72, 3317-3319	3.4	140
282	Influence of Si-doping on the characteristics of InGaN-GaN multiple quantum-well blue light emitting diodes. <i>IEEE Journal of Quantum Electronics</i> , 2002 , 38, 446-450	2	135
281	GaN metal-semiconductor-metal ultraviolet photodetectors with transparent indium-tin-oxide Schottky contacts. <i>IEEE Photonics Technology Letters</i> , 2001 , 13, 848-850	2.2	131
280	Low-operation voltage of InGaN-GaN light-emitting diodes with Si-doped In/sub 0.3/Ga/sub 0.7/N/GaN short-period superlattice tunneling contact layer. <i>IEEE Electron Device Letters</i> , 2001 , 22, 460-462	4.4	118
279	InGaN-AlInGaN multiquantum-well LEDs. <i>IEEE Photonics Technology Letters</i> , 2001 , 13, 559-561	2.2	96
278	GaN metal-semiconductor-metal ultraviolet sensors with various contact electrodes. <i>IEEE Sensors Journal</i> , 2002 , 2, 366-371	4	91
277	Nitride-based LEDs with 800/spl deg/C grown p-AlInGaN-GaN double-cap layers. <i>IEEE Photonics Technology Letters</i> , 2004 , 16, 1447-1449	2.2	90
276	n-UV+Blue/Green/Red White Light Emitting Diode Lamps. <i>Japanese Journal of Applied Physics</i> , 2003 , 42, 2284-2287	1.4	84
275	GaN metal-semiconductor-metal photodetectors with low-temperature-GaN cap layers and ITO metal contacts. <i>IEEE Electron Device Letters</i> , 2003 , 24, 212-214	4.4	84
274	The doping process and dopant characteristics of GaN. <i>Journal of Physics Condensed Matter</i> , 2002 , 14, R657-R702	1.8	78
273	Enhanced efficiency of GaN-based light-emitting diodes with periodic textured Ga-doped ZnO transparent contact layer. <i>Applied Physics Letters</i> , 2007 , 90, 263511	3.4	74
272	White-light emission from InGaN-GaN multiquantum-well light-emitting diodes with Si and Zn codoped active well layer. <i>IEEE Photonics Technology Letters</i> , 2002 , 14, 450-452	2.2	73
271	Nitride-based cascade near white light-emitting diodes. <i>IEEE Photonics Technology Letters</i> , 2002 , 14, 908-910	2.1	69
270	Nonalloyed Cr/Au-based Ohmic contacts to n-GaN. <i>Applied Physics Letters</i> , 2007 , 91, 182106	3.4	67
269	Enhanced light output of GaN-based power LEDs with transparent Al-doped ZnO current spreading layer. <i>IEEE Photonics Technology Letters</i> , 2006 , 18, 274-276	2.2	67

268	Nitride-based LEDs with an SPS tunneling contact Layer and an ITO transparent contact. <i>IEEE Photonics Technology Letters</i> , 2004 , 16, 1002-1004	2.2	67
267	Lateral epitaxial patterned sapphire InGaN/GaN MQW LEDs. <i>Journal of Crystal Growth</i> , 2004 , 261, 466-470	6	63
266	Nitride-based light emitting diodes with indium tin oxide electrode patterned by imprint lithography. <i>Applied Physics Letters</i> , 2007 , 91, 013504	3.4	60
265	High efficiency and improved ESD characteristics of GaN-based LEDs with naturally textured surface grown by MOCVD. <i>IEEE Photonics Technology Letters</i> , 2006 , 18, 1213-1215	2.2	60
264	Demonstration of GaN-Based Solar Cells With GaN/InGaN Superlattice Absorption Layers. <i>IEEE Electron Device Letters</i> , 2009 , 30, 225-227	4.4	59
263	Ohmic contacts to p-type GaN mediated by polarization fields in thin In _x Ga _{1-x} N capping layers. <i>Applied Physics Letters</i> , 2002 , 80, 986-988	3.4	57
262	High-efficiency InGaN-GaN MQW green light-emitting diodes with CART and DBR structures. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2002 , 8, 284-288	3.8	56
261	Improved ESD protection by combining InGaN-GaN MQW LEDs with GaN Schottky diodes. <i>IEEE Electron Device Letters</i> , 2003 , 24, 129-131	4.4	56
260	Enhanced AlGaIn/GaN MOS-HEMT Performance by Using Hydrogen Peroxide Oxidation Technique. <i>IEEE Transactions on Electron Devices</i> , 2013 , 60, 213-220	2.9	55
259	Effect of Thermal Annealing on Ga-Doped ZnO Films Prepared by Magnetron Sputtering. <i>Journal of the Electrochemical Society</i> , 2007 , 154, H521	3.9	55
258	InGaN/GaN light emitting diodes activated in O ₂ /ambient. <i>IEEE Electron Device Letters</i> , 2002 , 23, 240-242	4.4	53
257	In _{0.23} Ga _{0.77} N/GaN MQW LEDs with a low temperature GaN cap layer. <i>Solid-State Electronics</i> , 2003 , 47, 2027-2030	1.7	52
256	Effect of low-temperature-grown GaN cap layer on reduced leakage current of GaN Schottky diodes. <i>Applied Physics Letters</i> , 2005 , 86, 052103	3.4	49
255	Nitride-based near-ultraviolet LEDs with an ITO transparent contact. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2004 , 106, 69-72	3.1	49
254	ICP etching of sapphire substrates. <i>Optical Materials</i> , 2005 , 27, 1171-1174	3.3	49
253	High brightness green light emitting diodes with charge asymmetric resonance tunneling structure. <i>IEEE Electron Device Letters</i> , 2002 , 23, 130-132	4.4	49
252	n ⁺ -GaN formed by Si implantation into p-GaN. <i>Journal of Applied Physics</i> , 2002 , 91, 1845-1848	2.5	49
251	Enhanced output power in GaN-based LEDs with naturally textured surface grown by MOCVD. <i>IEEE Electron Device Letters</i> , 2005 , 26, 464-466	4.4	48

250	InGaN/GaN tunnel-injection blue light-emitting diodes. <i>IEEE Transactions on Electron Devices</i> , 2002 , 49, 1093-1095	2.9	48
249	Carrier dynamics in nitride-based light-emitting p-n junction diodes with two active regions emitting at different wavelengths. <i>Journal of Applied Physics</i> , 2003 , 94, 2167-2172	2.5	48
248	High-Speed GaN-Based Green Light-Emitting Diodes With Partially n-Doped Active Layers and Current-Confined Apertures. <i>IEEE Electron Device Letters</i> , 2008 , 29, 158-160	4.4	47
247	Enhancement in light output of InGaN-based microhole array light-emitting diodes. <i>IEEE Photonics Technology Letters</i> , 2005 , 17, 1163-1165	2.2	43
246	GaN Schottky barrier photodetectors with a low-temperature GaN cap layer. <i>Applied Physics Letters</i> , 2003 , 82, 2913-2915	3.4	42
245	Low-operation voltage of InGaN/GaN light-emitting diodes by using a Mg-doped Al/sub 0.15/Ga/sub 0.85/N/GaN superlattice. <i>IEEE Electron Device Letters</i> , 2001 , 22, 160-162	4.4	42
244	Electroluminescence efficiency of blue InGaN/GaN quantum-well diodes with and without an n-InGaN electron reservoir layer. <i>Journal of Applied Physics</i> , 2006 , 100, 113105	2.5	39
243	InGaN light-emitting diodes with naturally formed truncated micropylamids on top surface. <i>Applied Physics Letters</i> , 2006 , 88, 113505	3.4	39
242	Schottky barrier heights of metal contacts to n-type gallium nitride with low-temperature-grown cap layer. <i>Applied Physics Letters</i> , 2006 , 88, 032103	3.4	39
241	Investigation of the mechanism for Ti/Al ohmic contact on etched n-GaN surfaces. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2000 , 18, 729		38
240	Enhancement in output power of blue gallium nitride-based light-emitting diodes with omnidirectional metal reflector under electrode pads. <i>Applied Physics Letters</i> , 2008 , 93, 103507	3.4	37
239	Planar GaN n+ β photodetectors formed by Si implantation into p-GaN. <i>Applied Physics Letters</i> , 2002 , 81, 4263-4265	3.4	37
238	THz acoustic phonon spectroscopy and nanoscopy by using piezoelectric semiconductor heterostructures. <i>Ultrasonics</i> , 2015 , 56, 52-65	3.5	36
237	Probing hydrophilic interface of solid/liquid-water by nanoultrasonics. <i>Scientific Reports</i> , 2014 , 4, 6249	4.9	36
236	Laser-induced periodic structures for light extraction efficiency enhancement of GaN-based light emitting diodes. <i>Optics Express</i> , 2012 , 20, 5689-95	3.3	35
235	Reduction of dark current in AlGaIn-GaN Schottky-barrier photodetectors with a low-temperature-grown GaN cap layer. <i>IEEE Electron Device Letters</i> , 2004 , 25, 593-595	4.4	35
234	Characterization of GaN Schottky barrier photodetectors with a low-temperature GaN cap layer. <i>Journal of Applied Physics</i> , 2003 , 94, 1753-1757	2.5	35
233	High-performance GaN metal-insulator-semiconductor ultraviolet photodetectors using gallium oxide as gate layer. <i>Optics Express</i> , 2011 , 19, 12658-63	3.3	34

232	Characterization of Si implants in p-type GaN. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2002 , 8, 767-772	3.8	34
231	Enhanced output power in an InGaN-GaN multiquantum-well light-emitting diode with an InGaN current-spreading layer. <i>IEEE Photonics Technology Letters</i> , 2001 , 13, 1164-1166	2.2	34
230	GaN-Based Miniaturized Cyan Light-Emitting Diodes on a Patterned Sapphire Substrate With Improved Fiber Coupling for Very High-Speed Plastic Optical Fiber Communication. <i>IEEE Photonics Journal</i> , 2012 , 4, 1520-1529	1.8	33
229	Effect of Thickness of the p-AlGaIn Electron Blocking Layer on the Improvement of ESD Characteristics in GaN-Based LEDs. <i>IEEE Photonics Technology Letters</i> , 2008 , 20, 1142-1144	2.2	33
228	Nitride-based LEDs with modulation-doped Al/sub 0.12/Ga/sub 0.88/N-GaN superlattice structures. <i>IEEE Transactions on Electron Devices</i> , 2004 , 51, 1743-1746	2.9	33
227	Indium tin oxide ohmic contact to highly doped n-GaN. <i>Solid-State Electronics</i> , 1999 , 43, 2081-2084	1.7	33
226	Improved Reliability and ESD Characteristics of Flip-Chip GaN-Based LEDs With Internal Inverse-Parallel Protection Diodes. <i>IEEE Electron Device Letters</i> , 2007 , 28, 346-349	4.4	32
225	Improvement of near-ultraviolet InGaIn-GaN light-emitting diodes with an AlGaIn electron-blocking layer grown at low temperature. <i>IEEE Photonics Technology Letters</i> , 2003 , 15, 1342-1344	2.2	32
224	Ga-Doped ZnO Transparent Conductive Oxide Films Applied to GaN-Based Light-Emitting Diodes for Improving Light Extraction Efficiency. <i>IEEE Journal of Quantum Electronics</i> , 2008 , 44, 1211-1218	2	31
223	Emission Mechanism of Mixed-Color InGaIn/GaN Multi-Quantum-Well Light-Emitting Diodes. <i>Japanese Journal of Applied Physics</i> , 2006 , 45, 2463-2466	1.4	31
222	Improved Performance of GaN-Based Blue LEDs With the InGaIn Insertion Layer Between the MQW Active Layer and the n-GaN Cladding Layer. <i>IEEE Journal of Quantum Electronics</i> , 2010 , 46, 513-517	2	30
221	A curvature-tunable random laser. <i>Nanoscale</i> , 2019 , 11, 3534-3545	7.7	28
220	The improvement in modulation speed of GaN-based Green light-emitting diode (LED) by use of n-type barrier doping for plastic optical fiber (POF) communication. <i>IEEE Photonics Technology Letters</i> , 2006 , 18, 1636-1638	2.2	28
219	Luminescence of an InGaIn/GaN multiple quantum well light-emitting diode. <i>Solid-State Electronics</i> , 2000 , 44, 1055-1058	1.7	28
218	GaN-based light emitting diodes with embedded SiO ₂ pillars and air gap array structures. <i>Applied Physics Letters</i> , 2010 , 97, 081103	3.4	27
217	Ultraviolet band-pass Schottky barrier photodetectors formed by Al-doped ZnO contacts to n-GaN. <i>Applied Physics Letters</i> , 2006 , 88, 043506	3.4	27
216	. <i>IEEE Sensors Journal</i> , 2006 , 6, 406-411	4	27
215	High brightness InGaIn green LEDs with an ITO on n/sup +/-SPS upper contact. <i>IEEE Transactions on Electron Devices</i> , 2003 , 50, 2208-2212	2.9	27

214	InGaN-based epitaxial films as photoelectrodes for hydrogen generation through water photoelectrolysis and CO ₂ reduction to formic acid. <i>Solar Energy Materials and Solar Cells</i> , 2017 , 166, 86-90	6.4	26
213	Enhancing UV-emissions through optical and electronic dual-function tuning of Ag nanoparticles hybridized with n-ZnO nanorods/p-GaN heterojunction light-emitting diodes. <i>Nanoscale</i> , 2016 , 8, 4463-74	7.7	26
212	Si and Zn co-doped InGaN-GaN white light-emitting diodes. <i>IEEE Transactions on Electron Devices</i> , 2003 , 50, 519-521	2.9	26
211	III-Nitride-Based Cyan Light-Emitting Diodes With GHz Bandwidth for High-Speed Visible Light Communication. <i>IEEE Electron Device Letters</i> , 2016 , 1-1	4.4	25
210	Slanted n-ZnO/p-GaN nanorod arrays light-emitting diodes grown by oblique-angle deposition. <i>APL Materials</i> , 2014 , 2, 056101	5.7	24
209	Low Operation Voltage of Nitride-Based LEDs with Al-Doped ZnO Transparent Contact Layer. <i>Electrochemical and Solid-State Letters</i> , 2008 , 11, H269		24
208	Effect of the Electrode Pattern on Current Spreading and Driving Voltage in a GaN Sapphire LED Chip. <i>Journal of the Electrochemical Society</i> , 2008 , 155, H836	3.9	24
207	Improving efficiency of InGaN/GaN multiple quantum well solar cells using CdS quantum dots and distributed Bragg reflectors. <i>Solar Energy Materials and Solar Cells</i> , 2013 , 117, 531-536	6.4	23
206	Inverted Al _{0.25} Ga _{0.75} N/GaN ultraviolet p-i-n photodiodes formed on p-GaN template layer grown by metalorganic vapor phase epitaxy. <i>Applied Physics Letters</i> , 2010 , 97, 013502	3.4	23
205	Enhancement of the conversion efficiency of GaN-based photovoltaic devices with AlGaN/InGaN absorption layers. <i>Applied Physics Letters</i> , 2010 , 97, 021113	3.4	23
204	Effects of Thermal Annealing on Al-Doped ZnO Films Deposited on p-Type Gallium Nitride. <i>Journal of the Electrochemical Society</i> , 2006 , 153, G296	3.9	23
203	Nitride-based green light-emitting diodes with high temperature GaN barrier layers. <i>IEEE Transactions on Electron Devices</i> , 2003 , 50, 1766-1770	2.9	23
202	Design of Hole-Blocking and Electron-Blocking Layers in Al _x Ga _{1-x} N-Based UV Light-Emitting Diodes. <i>IEEE Transactions on Electron Devices</i> , 2016 , 63, 1141-1147	2.9	21
201	InGaN gallium nitride light-emitting diodes with reflective electrode pads and textured gallium-doped ZnO contact layer. <i>Applied Physics Letters</i> , 2010 , 96, 133504	3.4	21
200	A Numerical Study of Thermal and Electrical Effects in a Vertical LED Chip. <i>Journal of the Electrochemical Society</i> , 2010 , 157, H31	3.9	21
199	Photodetectors formed by an indium tin oxide/zinc oxide/p-type gallium nitride heterojunction with high ultraviolet-to-visible rejection ratio. <i>Applied Physics Letters</i> , 2009 , 94, 013512	3.4	21
198	Ultraviolet bandpass Al _{0.17} Ga _{0.83} N/GaN heterojunction phototransistors with high optical gain and high rejection ratio. <i>Applied Physics Letters</i> , 2008 , 92, 053506	3.4	21
197	Nitride-based blue LEDs with GaN/SiN double buffer layers. <i>Solid-State Electronics</i> , 2003 , 47, 2019-2022	1.7	21

196	Ga ₂ O ₃ Films for Photoelectrochemical Hydrogen Generation. <i>Journal of the Electrochemical Society</i> , 2014 , 161, H508-H511	3.9	20
195	Observation of dislocation etch pits in epitaxial lateral overgrowth GaN by wet etching. <i>Solid-State Electronics</i> , 2002 , 46, 555-558	1.7	20
194	GaN p-n junction diode formed by Si ion implantation into p-GaN. <i>Solid-State Electronics</i> , 2002 , 46, 2179-2183	1.8	20
193	White emission from non-planar InGaN/GaN MQW LEDs grown on GaN template with truncated hexagonal pyramids. <i>Optics Express</i> , 2015 , 23, A401-12	3.3	19
192	Electrical-optical analysis of a GaN/sapphire LED chip by considering the resistivity of the current-spreading layer. <i>Optical Review</i> , 2009 , 16, 213-215	0.9	19
191	Ultraviolet/blue light-emitting diodes based on single horizontal ZnO microrod/GaN heterojunction. <i>Nanoscale Research Letters</i> , 2014 , 9, 446	5	18
190	Visible-blind GaN p-n photodiodes with an Al _{0.12} Ga _{0.88} N/GaN superlattice structure. <i>Solid-State Electronics</i> , 2003 , 47, 873-878	1.7	18
189	Passively gain-switched and self mode-locked thulium fiber laser at 1950 nm. <i>Optics and Laser Technology</i> , 2014 , 56, 354-357	4.2	17
188	Femtosecond ultrasonic spectroscopy using a piezoelectric nanolayer: Hypersound attenuation in vitreous silica films. <i>Applied Physics Letters</i> , 2011 , 99, 051913	3.4	17
187	GaN-Based LEDs With AZO:Y Upper Contact. <i>IEEE Transactions on Electron Devices</i> , 2010 , 57, 134-139	2.9	17
186	Ultraviolet band-pass photodetectors formed by Ga-doped ZnO contacts to n-GaN. <i>Applied Physics Letters</i> , 2008 , 92, 113512	3.4	17
185	Experimental study of perpendicular transport in weakly coupled Al _x Ga _{1-x} N/GaN superlattices. <i>Applied Physics Letters</i> , 2003 , 83, 4975-4977	3.4	17
184	Deep level defect in Si-implanted GaN n+-p junction. <i>Applied Physics Letters</i> , 2003 , 82, 3671-3673	3.4	17
183	Polymer PBT/n-GaN metal-insulator-semiconductor structure. <i>Applied Physics Letters</i> , 2001 , 79, 4589-4591	3.4	17
182	AlGaN ultraviolet metal-semiconductor-metal photodetectors grown on Si substrates. <i>Sensors and Actuators A: Physical</i> , 2007 , 135, 502-506	3.9	16
181	Comparison of low-temperature GaN, SiO ₂ , and SiN _x as gate insulators on AlGaN/GaN heterostructure field-effect transistors. <i>Journal of Applied Physics</i> , 2005 , 98, 064506	2.5	16
180	Vertical InGaN-based green-band solar cells operating under high solar concentration up to 300 suns. <i>Optics Express</i> , 2014 , 22 Suppl 5, A1222-8	3.3	15
179	Improved conversion efficiency of GaN-based solar cells with Mn-doped absorption layer. <i>Applied Physics Letters</i> , 2013 , 103, 063906	3.4	15

178	Thermal Boundary Resistance between GaN and Cubic Ice and THz Acoustic Attenuation Spectrum of Cubic Ice from Complex Acoustic Impedance Measurements. <i>Physical Review Letters</i> , 2013 , 111, 225907-14	7.4	15
177	Temperature-dependent study of n-ZnO β -GaN diodes. <i>Applied Physics Letters</i> , 2007 , 90, 132111	3.4	15
176	Warm-white light-emitting diode with high color rendering index fabricated by combining trichromatic InGaN emitter with single red phosphor. <i>Optics Express</i> , 2015 , 23, A232-9	3.3	14
175	Improved Output Power of GaN-based Blue LEDs by Forming Air Voids on Ar-Implanted Sapphire Substrate. <i>Journal of Lightwave Technology</i> , 2013 , 31, 1318-1322	4	14
174	Characteristics of InGaN-based concentrator solar cells operating under 150X solar concentration. <i>Optics Express</i> , 2011 , 19 Suppl 4, A695-700	3.3	14
173	Effect of Cl ₂ /Ar dry etching on p-GaN with Ni/Au metallization characterization. <i>Applied Physics Letters</i> , 2005 , 87, 252107	3.4	14
172	Low-resistance Ni/Au ohmic contact to Mg-doped of Al _{0.15} Ga _{0.85} N/GaN superlattices. <i>Solid-State Electronics</i> , 2001 , 45, 717-720	1.7	14
171	Mn valence state mediated room temperature ferromagnetism in nonpolar Mn doped GaN. <i>Applied Surface Science</i> , 2019 , 473, 693-698	6.7	14
170	GaN-Based Planar p-i-n Photodetectors With the Be-Implanted Isolation Ring. <i>IEEE Transactions on Electron Devices</i> , 2013 , 60, 1178-1182	2.9	13
169	. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2009 , 15, 1275-1280	3.8	13
168	Mn-doped GaN as photoelectrodes for the photoelectrolysis of water under visible light. <i>Optics Express</i> , 2012 , 20 Suppl 5, A678-83	3.3	13
167	GaN-based light emitting diodes with micro- and nano-patterned structures by femtosecond laser nonlinear decomposition. <i>Applied Physics Letters</i> , 2012 , 101, 131103	3.4	13
166	Linear Cascade Arrays of GaN-Based Green Light-Emitting Diodes for High-Speed and High-Power Performance. <i>IEEE Photonics Technology Letters</i> , 2007 , 19, 1368-1370	2.2	13
165	Phosphor-Free GaN-Based Transverse Junction Light Emitting Diodes for the Generation of White Light. <i>IEEE Photonics Technology Letters</i> , 2006 , 18, 2593-2595	2.2	13
164	Si diffusion in p-GaN. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2004 , 22, 1727		13
163	Hydrogen gas generation using n-GaN photoelectrodes with immersed Indium Tin Oxide ohmic contacts. <i>Optics Express</i> , 2011 , 19 Suppl 6, A1196-201	3.3	12
162	Investigation of the Carrier Dynamic in GaN-Based Cascade Green Light-Emitting Diodes Using the Very Fast Electrical/Optical Pump/Probe Technique. <i>IEEE Transactions on Electron Devices</i> , 2011 , 58, 495-500	2.9	12
161	Femtosecond excitation of radial breathing mode in 2-D arrayed GaN nanorods. <i>Optics Express</i> , 2012 , 20, 16611	3.3	12

160	Phosphor-Free GaN-Based Transverse Junction White-Light Light-Emitting Diodes With Regrown n-Type Regions. <i>IEEE Photonics Technology Letters</i> , 2008 , 20, 449-451	2.2	12
159	Improved performance of planar GaN-based p-i-n photodetectors with Mg-implanted isolation ring. <i>Applied Physics Letters</i> , 2006 , 89, 183509	3.4	12
158	AlGaIn/GaN Schottky-barrier UV-B bandpass photodetectors with ITO contacts and LT-GaN cap layers. <i>Semiconductor Science and Technology</i> , 2006 , 21, 1064-1068	1.8	12
157	Highly Reliable Nitride-Based LEDs With Internal ESD Protection Diodes. <i>IEEE Transactions on Device and Materials Reliability</i> , 2006 , 6, 442-447	1.6	12
156	Improvement of InGaIn/GaN laser diodes by using a Si-doped In/sub 0.23/Ga/sub 0.77/N/GaN short-period superlattice tunneling contact layer. <i>IEEE Electron Device Letters</i> , 2003 , 24, 206-208	4.4	12
155	Manganese-doped AlGaIn/GaN heterojunction solar cells with intermediate band absorption. <i>Solar Energy Materials and Solar Cells</i> , 2016 , 157, 727-732	6.4	11
154	InGaIn working electrodes with assisted bias generated from GaAs solar cells for efficient water splitting. <i>Optics Express</i> , 2013 , 21 Suppl 6, A991-6	3.3	11
153	Effect of Growth Pressure of Undoped GaN Layer on the ESD Characteristics of GaN-Based LEDs Grown on Patterned Sapphire. <i>IEEE Photonics Technology Letters</i> , 2011 , 23, 968-970	2.2	11
152	Improved Hydrogen Gas Generation Rate of n-GaN Photoelectrode with SiO ₂ Protection Layer on the Ohmic Contacts from the Electrolyte. <i>Journal of the Electrochemical Society</i> , 2010 , 157, B2668-9	3.9	11
151	Influence of modulated fields on the Landau level properties of graphene. <i>Physical Review B</i> , 2011 , 83,	3.3	11
150	Linear Cascade GaN-Based Green Light-Emitting Diodes With Invariant High-Speed/Power Performance Under High-Temperature Operation. <i>IEEE Photonics Technology Letters</i> , 2008 , 20, 1896-1898	3.2	11
149	In Situ Monitoring of Chemical Reactions at a Solid-Water Interface by Femtosecond Acoustics. <i>Journal of Physical Chemistry Letters</i> , 2017 , 8, 5430-5437	6.4	10
148	Light-emitting diodes with surface gallium nitride p-n homojunction structure formed by selective area regrowth. <i>Scientific Reports</i> , 2019 , 9, 3243	4.9	10
147	Gallium nitride-based light-emitting diodes with embedded air voids grown on Ar-implanted AlN/sapphire substrate. <i>Applied Physics Letters</i> , 2012 , 101, 151103	3.4	10
146	Numerical study of the suppressed efficiency droop in blue InGaIn LEDs with polarization-matched configuration. <i>Optics Letters</i> , 2013 , 38, 3158-61	3	10
145	High-Brightness InGaIn/GaN Power Flip-Chip LEDs. <i>Journal of Lightwave Technology</i> , 2009 , 27, 1985-1989	4	10
144	Improved Light Extraction Efficiency in AlGaInP Light-Emitting Diodes by Applying a Periodic Texture on the Surface. <i>IEEE Photonics Technology Letters</i> , 2008 , 20, 1724-1726	2.2	10
143	GaN diffractive microlenses fabricated with gray-level mask. <i>Optics Communications</i> , 2003 , 215, 75-78	2	10

142	Characterization of p-type In _x Ga _{1-x} N grown by metalorganic chemical vapor deposition. <i>Solid-State Electronics</i> , 2001 , 45, 427-430	1.7	10
141	AlGaInP/GaP Light-Emitting Diodes Fabricated by Wafer Direct Bonding Technology. <i>Japanese Journal of Applied Physics</i> , 1996 , 35, 4199-4202	1.4	10
140	Rationally designed RGO@CuO@Mn ₂ O ₃ as an excellent electrocatalyst for the rapid and real-time detection of 2-nitrophenol. <i>New Journal of Chemistry</i> , 2020 , 44, 12465-12472	3.6	10
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